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#6/Amold R (NE)
Defect
10/19/01

Patent
Attorney's Docket No. 033277-004

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
Nadim HADDAD et al) Group Art Unit: 2812
Application No.: 09/629,172) Examiner: R. Pompey
Filed: July 31, 2000)
For: METHOD TO HARDEN SHALLOW)
TRENCH ISOLATION AGAINST)
TOTAL IONIZING DOSE RADIATION)

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

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Date of Deposit 10/15/01
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20231.
Richard J. McGrath
(Typed or printed name of person mailing paper or fee)
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Sir:

In response to the Office Action dated July 6, 2001, please amend the above-identified
patent application as follows:

IN THE CLAIMS:

Please cancel claim 6 and substitute amended claims 1 and 7 as follows:

1. (Amended) A method for fabricating radiation-tolerant integrated circuit devices, said
method comprising:

depositing a layer of pad oxide on a semiconductor substrate;

selectively etching said pad oxide layer and said semiconductor substrate to define a
trench within said semiconductor substrate;

implanting boron ions at an angle with respect to normal in said trench; and

implanting an electrically neutral material into said substrate.

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